

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

2SC2236

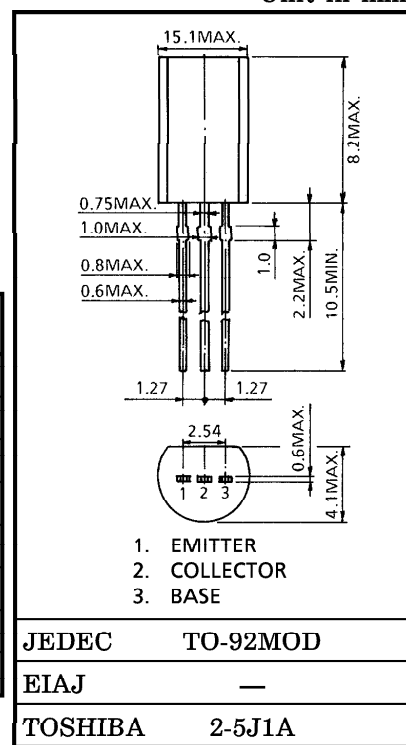
AUDIO POWER AMPLIFIER APPLICATIONS.

Unit in mm

- Complementary to 2SA966 and 3 Watts Output Applications.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	30	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	1.5	A
Base Current	I_B	0.15	A
Collector Power Dissipation	P_C	900	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C



ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Weight : 0.36g

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=30V, I_E=0$	—	—	100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$	—	—	100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	30	—	—	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=1mA, I_C=0$	5	—	—	V
DC Current Gain	h_{FE} (Note)	$V_{CE}=2V, I_C=500mA$	100	—	320	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=1.5A, I_B=0.03A$	—	—	2.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=2V, I_C=500mA$	—	—	1.0	V
Transition Frequency	f_T	$V_{CE}=2V, I_C=500mA$	—	120	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$	—	—	30	pF

Note : h_{FE} Classification O : 100~200, Y : 160~320

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